CELL LIBRARY FOR SPEED-INDEPENDENT VLSI

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Main features of SI-circuits

 Speed-Independent (SI) circuits excel synchronous ones in:
Robustness to variation of electrophysical parameters or to their degradation

Operation safety and validity of the data processing results
High performance, that is maximum possible at any real environment and IPI Rata EWDTS-2015



Peculiarities of SI-circuits

- Two-phase discipline: work and spacer (pause)
- Indication of each operation phase
- Acknowledge-require technique of interaction between SI-units
- An arbitrary duration of each phase

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Specific circuit base for SI-units

All cells for designing SIcircuits must be single-stage one or have an output indicating all interior signals Their inputs and outputs take only logical 0 and 1 values

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Library's content

Combinational logic Triggers Counters Multiplexers Adders Code converters Indicators

Bit of binary counter



Interface cells: latch



D - unary data input; E - write enable input with null spacer; R asynchronous reset EWDTS-2015 9

Interface cells: flip-flop



D - unary data input; E - write enable input with null spacer; R asynchronous reset IPI RAS 10

Interface cells: flip-flop



Cells with forced output: latch



Cells with forced output: flip-flop



R, S - dual-rail data input; C - self-timed reset; Q, QB - forced output IPI RAS EWDTS-2015 13

Indication cells: hysteresis triggers



10, 11 - indication signals EWDTS-2015

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Indication cells: combined logic



IO, II - indication signals; B*,B*B - bi-phase data signals IPI RAS EWDTS-2015

Library characterization

 Self-timed feature analysis (ASPECT)
Automatic calculation of the electrical and timing parameters (STERH)

 Model files in LIBERTY and Verilog formats (STERH)
Integration with modern industrial IPI ADS EWDTS-2015 16

Cell library approbation

Various CMOS standard processes: *1.5 µm for semicustom circuits (Microcore, 14 000 transistors), ♦ 0.18 µm for semicustom circuits (Microcore, 17 000 transistors), ♦ 0.18 µm for custom VLSI (Square-Root & Divider, 77 000 transistors), *65 nm for custom VLSI (Square-Root & Divider, 77 000 transistors; Fused Multiply-Add Unit, 315 000 transistors)



Increase of steady operation range (10-15 times); decrease of energy consumption (30-50%); rise of performance (100-250%); detection of constant malfunctions (up to 100%)

Conclusions

Suggested library: * Corresponds to the criteria of building SI-circuits, Contains more than 200 library cells expanding standard cell libraries, Provides really SI solutions for interfacing with synchronous environment and for driving large loads

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Thanks

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